



WBFBP-02L Plastic-Encapsulate Diodes

FRB751 Schottky barrier Diodes

DESCRIPTION

Silicon epitaxial planar

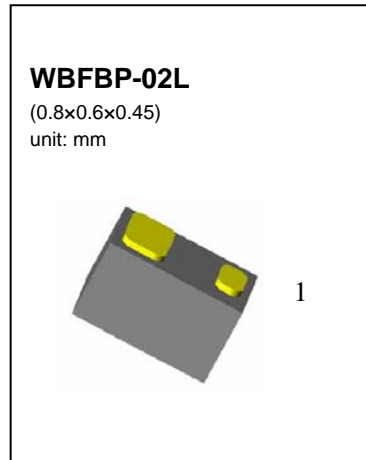
FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

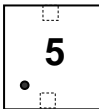
APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



MARKING: 5



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	30	mA
Peak forward surge current	I _{FSM}	150	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.37	V	I _F =1mA
Reverse current	I _R			0.5	μ A	V _R =30V
Capacitance between terminals	C _T		2		pF	V _R =1V,f=1MHZ

Typical Characteristics

● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

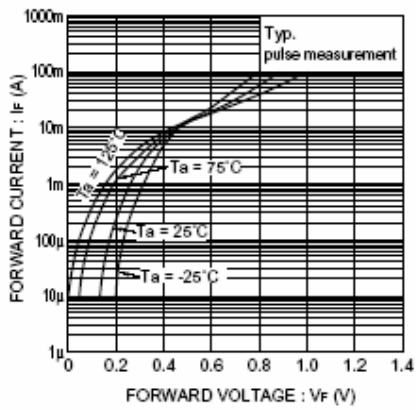


Fig. 1 Forward characteristics

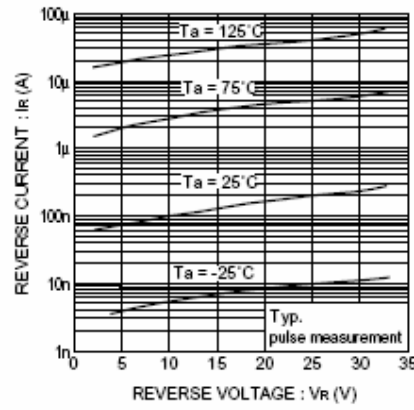


Fig. 2 Reverse characteristics

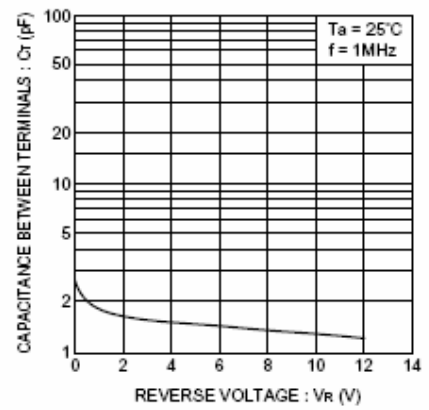
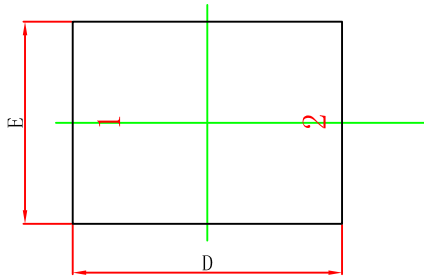


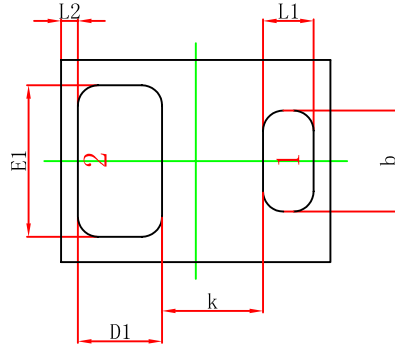
Fig. 3 Capacitance between terminals characteristics



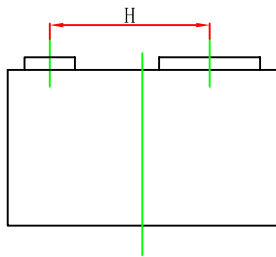
WBFBP-02L (0.8×0.6×0.45) PACKAGE OUTLINE DIMENSIONS



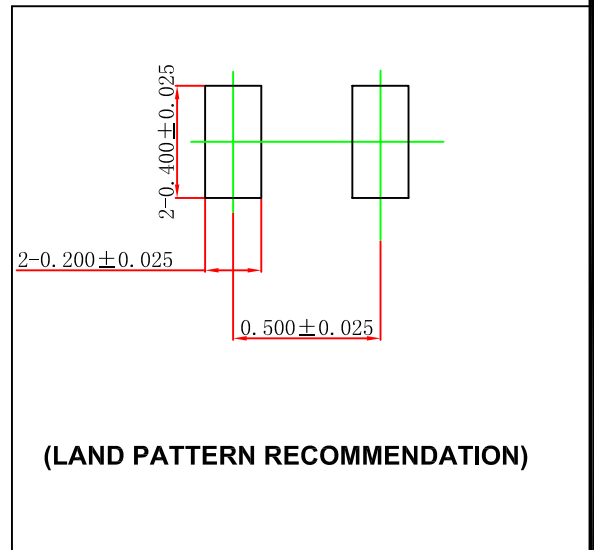
TOP VIEW



BOTTOM VIEW



SIDE VIEW



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
D	0.750	0.850	0.030	0.034
E	0.550	0.650	0.022	0.026
D1	0.220	0.320	0.009	0.013
E1	0.400	0.500	0.016	0.020
b	0.300 REF.		0.012 REF.	
H	0.440	0.540	0.017	0.021
k	0.28 REF.		0.011 REF.	
L1	0.100	0.200	0.004	0.008
L2	0.050 REF.		0.002 REF.	